

1 Characteristics

Table 1. Absolute maximum ratings (T_{amb} = 25 °C, unless otherwise specified)

Symbol	Parameter		Value	Unit
I	On state rms surrent (full sine ways) C = Fem²	T _{amb} = 76 °C	0.0	_
I _{T(RMS)}	On-state rms current (full sine wave), S = 5cm ²	T _{tab} = 104 °C	0.8	Α
I	Non repetitive surge peak on-state current	t _p = 20 ms	13	_
I _{TSM}	T _j initial = 25 °C, (full cycle sine wave)	t _p = 16.7 ms	13.7	Α
I ² t	l^2t for fuse selection t_p = 10 ms			A ² s
dI/dt	Critical rate of rise on-state current $I_G = 2 \times I_{GT}$, tr $\leq 100 \text{ ns}$ $f = 120 \text{ Hz}$, $T_j = 125 \text{ °C}$		100	A/µs
$V_{PP}^{(1)}$	Non repetitive line peak pulse voltage	2	kV	
P _{G(AV)}	Average gate power dissipation	T _j = 125 °C	0.1	W
V_{GM}	Peak positive gate voltage	T _j = 125 °C	10	V
I _{GM}	Peak gate current (t_p = 20 μ s) T_j = 125 °C		1	Α
T _{stg}	Storage temperature range	-40 to +150	°C	
Tj	Operating junction temperature range	-30 to +125	°C	

according to test described by standard IEC 61000-4-5, see Figure 17. Overvoltage ruggedness test circuit for resistive and inductive loads, T_{amb} = 25 °C (conditions equivalent to IEC 61000-4-5 standard) for conditions

Table 2. Electrical characteristics ($T_j = 25$ °C, unless otherwise specified)

Symbol	Test conditions	Quadrant	Value		Unit
I _{GT} ⁽¹⁾	V _{OUT} = 12 V, R _I = 33 Ω	II - III	Max.	10	mA
V _{GT}	VOUT = 12 V, INC = 33 12	11 - 111	Max.	1.0	V
V_{GD}	$V_{OUT} = V_{DRM}$, $R_L = 3.3 \text{ k}\Omega$, $T_j = 125 \text{ °C}$	11 - 111	Min.	0.15	V
I _H	I _{OUT} = 100 mA	Max.	10	mA	
IL	$I_G = 1.2 \times I_{GT}$	Max.	25	mA	
dV/dt	V_{OUT} = 402 V, gate open, T_j = 125 °C				V/µs
uv/ut	V_{OUT} = 536 V, gate open, T_j = 125 °C				v/µS
(dl/dt)c	Without snubber (15 V/ μ s), T _j = 125 °C, turn-off time \leq 20 ms	Min.	2	A/ms	
V _{CL}	$I_{CL} = 0.1 \text{ mA}, t_p = 1 \text{ ms}$			850	V

^{1.} Minimum I_{GT} is guaranteed at 10% of I_{GT} max.

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Table 3. Static electrical characteristics

Symbol	Test conditions			Value	Unit
V _{TM} ⁽¹⁾	I _{TM} = 1.1 A, t _p = 500 μs	T _j = 25 °C	Max.	1.3	V
V _{TO} ⁽¹⁾	Threshold voltage	T _j = 125 °C	Max.	0.85	V
R _d ⁽¹⁾	Dynamic resistance	T _j = 125 °C	Max.	300	mΩ
I _{DRM}	$V_{OUT} = V_{DRM} / V_{RRM}$	T _j = 25 °C	Max.	2	μA
I_{RRM}		T _j = 125 °C	ividX.	0.2	mA

^{1.} For both polarities of OUT pin referenced to COM pin

Table 4. Thermal characteristics

Symbol	Parame	Max. value	Unit		
R _{th(j-t)}	Junction to tab (AC)	25	°C/\\		
R _{th(j-a)}	Junction to ambient	S = 5 cm ²	Max.	60	°C/W

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1.1 Characteristics (curves)

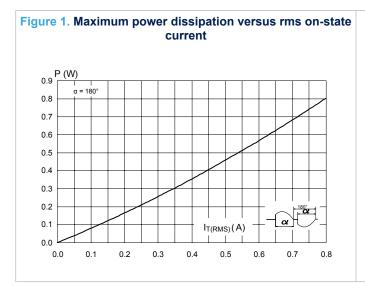
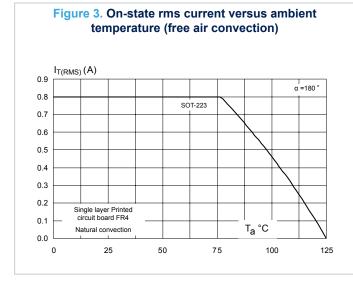


Figure 2. On-state rms current versus case temperature

0.9
0.8
0.7
0.6
0.5
0.4
0.3
0.2
0.1
0.0
0 25 50 75 100 125



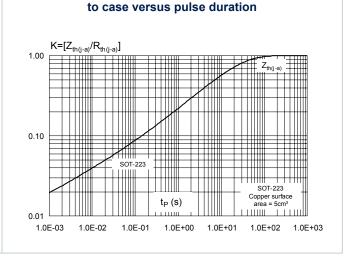


Figure 4. Relative variation of thermal impedance junction

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Figure 5. Relative variation of holding and latching current versus junction temperature

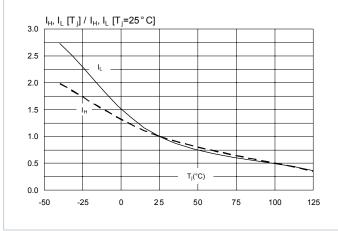


Figure 6. Relative variation of I_{GT} and V_{GT} versus junction temperature

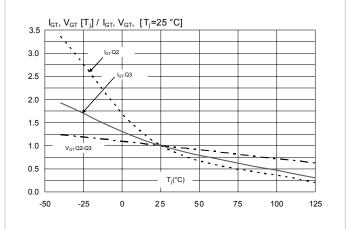


Figure 7. Surge peak on-state current versus number of cycles

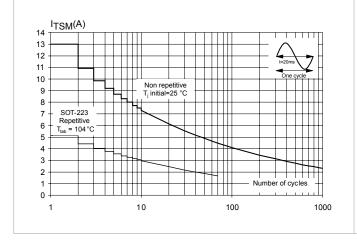


Figure 8. Non repetitive surge peak on-state current for a sinusoidal pulse

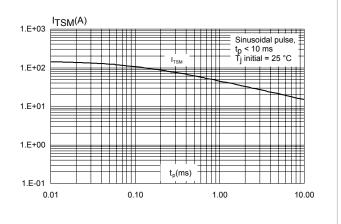


Figure 9. On-state characteristics (maximum values)

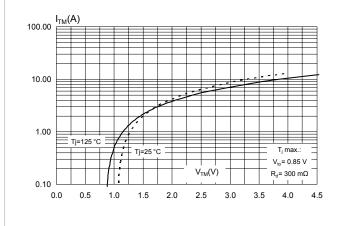
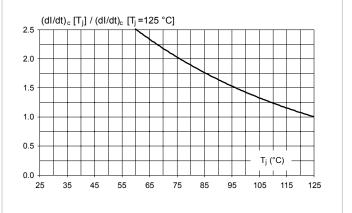


Figure 10. Relative variation of critical rate of decrease of main current versus junction temperature



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Figure 11. Relative variation of static dV/dt immunity versus junction temperature (typical values above 5 kV/µs)

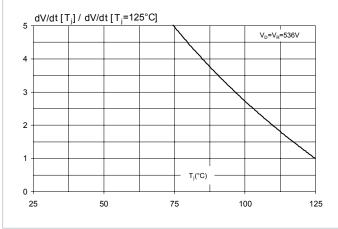


Figure 12. Relative variation of leakage current versus junction temperature

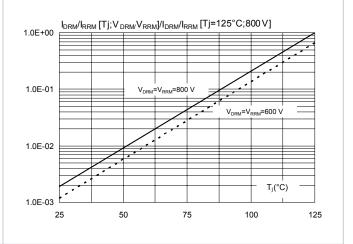


Figure 13. Relative variation of critical rate of decrease of main current (di/dt)c versus (dV/dt)c

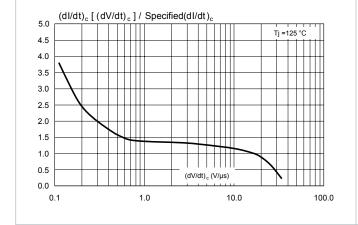
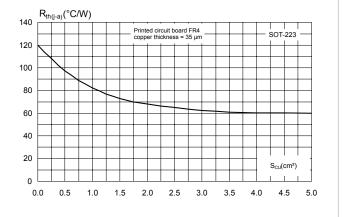


Figure 14. Thermal resistance junction to ambient versus copper surface under tab



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2 Alternating current mains switch - basic application

The ACS108 switch is triggered by a negative gate current flowing from the gate pin G. The switch can be driven directly by the digital controller through a resistor as shown in Figure 15. Typical application schematic

Thanks to its overvoltage protection and turn-off commutation performance, the ACS108 switch can drive a small power high inductive load with neither varistor nor additional turn-off snubber.

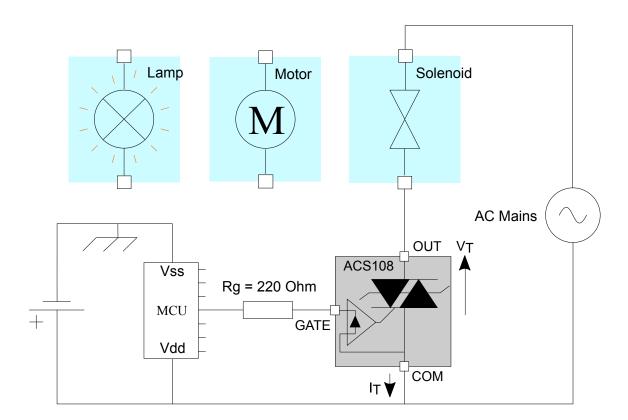


Figure 15. Typical application schematic

2.1 Protection against overvoltage: the best choice is ACS

In comparison with standard Triacs the ACS108 is over-voltage self-protected, as specified by the parameter V_{CL} . This feature is useful in two operating conditions: in case of turn-off of very inductive load, and in case of surge voltage that can occur on the electrical network.

2.1.1 High inductive load switch-off: turn-off overvoltage clamping

With high inductive and low rms current loads the rate of decrease of the current is very low. An overvoltage can occur when the gate current is removed and the OUT current is lower than I_H.

As shown in Figure 16. Switching off of a high inductive load - typical clamping capability of ACS108 (T_{amb} = 25 °C), at the end of the last conduction half-cycle, the load current decreases ① . The load current reaches the holding current level I_H ② , and the ACS turns off ③ . The water valve, as an inductive load (up to 15 H), reacts as a current generator and an overvoltage is created, which is clamped by the ACS ④ . The current flows through the ACS avalanche and decreases linearly to zero. During this time, the voltage across the switch is limited to the clamping voltage V_{CL} . The energy stored in the inductance of the load is dissipated in the clamping section that is

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designed for this purpose. When the energy has been dissipated, the ACS voltage falls back to the mains voltage value (230 V rms, 50 Hz) ⑤.

Figure 16. Switching off of a high inductive load - typical clamping capability of ACS108 (T_{amb} = 25 °C)

2.1.2 Alternating current mains transient voltage ruggedness

The ACS108 switch is able to withstand safely the AC mains transients either by clamping the low energy spikes or by breaking-over when subjected to high energy shocks, even with high turn-on current rises.

The test circuit shown in Figure 17. Overvoltage ruggedness test circuit for resistive and inductive loads, $T_{amb} = 25$ °C (conditions equivalent to IEC 61000-4-5 standard) is representative of the final ACS108 application, and is also used to test the AC switch according to the IEC 61000-4-5 standard conditions. Thanks to the load limiting the current, the ACS108 switch withstands the voltage spikes up to 2 kV above the peak mains voltage. The protection is based on an overvoltage crowbar technology. Actually, the ACS108 breaks over safely as shown in Figure 18. Typical current and voltage waveforms across the ACS108 (+2 kV surge, IEC 61000-4-5 standard). The ACS108 recovers its blocking voltage capability after the surge (switch off back at the next zero crossing of the current).

Such non-repetitive tests can be done 10 times on each AC mains voltage polarity.

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Figure 17. Overvoltage ruggedness test circuit for resistive and inductive loads, T_{amb} = 25 °C (conditions equivalent to IEC 61000-4-5 standard)

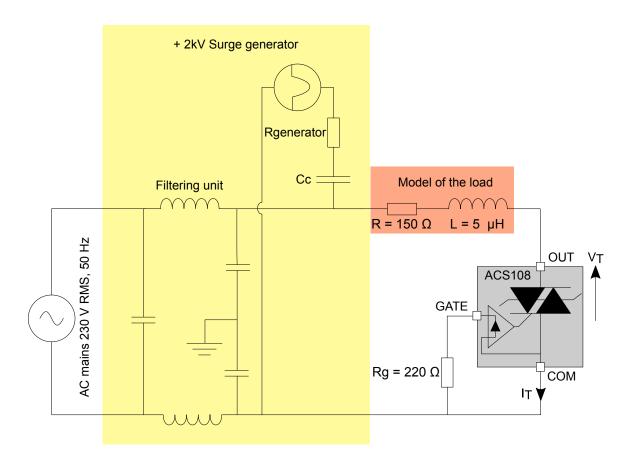
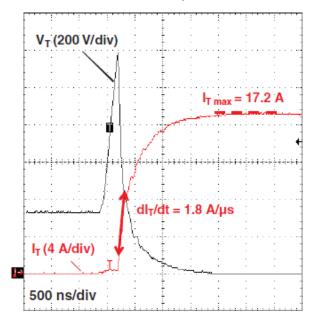


Figure 18. Typical current and voltage waveforms across the ACS108 (+2 kV surge, IEC 61000-4-5 standard)



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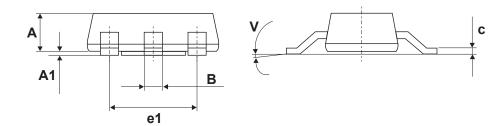
3 Package information

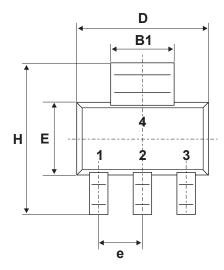
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

3.1 SOT-223 package information

- Epoxy meets UL94, V0
- Lead free plating + halogen-free molding resin

Figure 19. SOT-223 package outline





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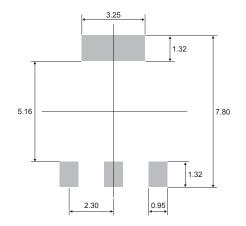


Table 5. SOT-223 package mechanical data

				Dimensions			
Ref.	Millimeters			Inches ⁽¹⁾			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А			1.80			0.0709	
A1		0.02	0.10		0.0008	0.0039	
В	0.60	0.70	0.85	0.024	0.0276	0.0335	
B1	2.90	3.00	3.15	0.114	0.1181	0.1240	
С	0.24	0.26	0.35	0.009	0.0102	0.0138	
D	6.30	6.50	6.70	0.248	0.2559	0.2638	
е		2.3			0.0906		
e1		4.6			0.1811		
Е	3.30	3.50	3.70	0.130	0.1378	0.1457	
Н	6.70	7.00	7.30	0.264	0.2756	0.2874	
V	10° max.						

^{1.} Inches only for reference

Figure 20. SOT-223 footprint (dimensions in mm)



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4 Ordering information

Figure 21. Ordering information scheme

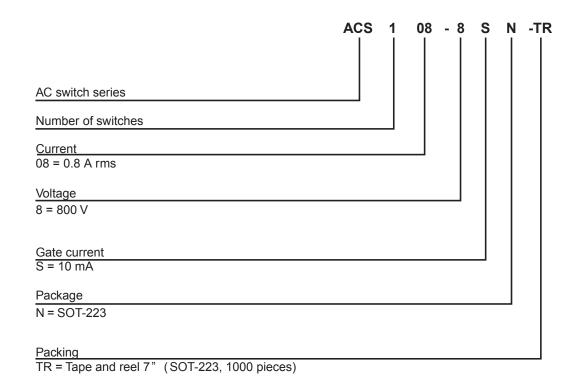


Table 6. Ordering information

Order code	Marking	Package	Weight	Base qty.	Packing mode
ACS108-8SN-TR	ACS 108 8S ⁽¹⁾	SOT-223	0.11 g	1000	Tape and reel

1. first row = ACS, second row = 108, third row = 8S

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Revision history

Table 7. Document revision history

Date	Version	Changes
07-Feb-2019	1	Initial release.
08-Aug-2019	2	Updated Section Product status link / summary.



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